	12, 22	11.+0	1	200
	ad X t	UT CS	Search leac	ו ב
				US-PGPUB; USPAT;
	IS&R	2	("4159417").PN.	Д
				DERWENT; IBM_TDB
			(" (Semiconductororsiliconorpolysilicon	US-PGPUB; USPAT;
2	IS&R	0	<u> </u>	USOCR; EPO; JPO;
			ium)near3substrate").PN.	DERWENT; IBM_TDB
				TIC-DCDITE. TICDAT.
<u></u>	υ υ	C L 30 V V	polysilicon or (silicon adj carbide)	
<u>1</u>	240	7 1 0 0 7 7	or sic or gaas or gallium) near3	DERWENT; IBM_TDB
				US-PGPUB; USPAT;
4	BRS	7933	sensor and display and S3	0; JPO
			1	$\mathbf{\Sigma}$
				US-PGPUB; USPAT;
വ	BRS	1232	(strain or gauge or gauges) and S4	USOCR; EPO; JPO;
				DERWENT; IBM_TDB
				US-PGPUB; USPAT;
9	BRS	419	(pixel or pixels) and S5	USOCR; EPO; JPO;
				DERWENT; IBM_TDB
				UB;
_	BRS	129	S6 and @ad<"19990701"	_
				DERWENT; IBM_TDB
				S
ω	BRS	190	S6 and @rlad<"19990701"	α
				DERWENT; IBM_TDB
ത	BRS	260	S7 S8	USOCR; EPO; JPO;
				DERWENT; IBM_TDB
			7	US-PGPUB; USPAT;
10	BRS	281	S3	USOCR; EPO; JPO;

	Type	Hits	Search Text	DBs
H	BRS	23	S10 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
12	BRS	22	S10 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
13	BRS	43	S11 S12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
14	BRS	32	(logic or cmos or process\$4) and S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
15	BRS	478	((solar near (cell or sensor)) nearl5 display) and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
19	BRS	143	S15 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
17	BRS	42	S15 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
18	BRS	164	S17 S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
10	BRS	1073	Mems near5 (integrat\$3) and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
20	BRS	85	S19 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB

	Type	Hits	Search Text	DBs
31	BRS	7.7	(display or led or leds or pixel or pixels) and S30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
32	BRS	126	mems.ti. and display	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
33	BRS	-	S32 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
34	BRS	9	S32 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
35	BRS	7	S33 S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
36	BRS	46	mems.ti. and LEd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
37	BRS	0	S36 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
38	BRS	3	S36 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
39	BRS	0	mems.ti. and "integrat\$4.ti"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
40	BRS	1406	mems.ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Туре	Hits	Search Text	DBs
41	BRS	276594	integrat\$4.ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
42	BRS	277910	S40 S41	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
43	BRS	90	S40 and S41	
44	BRS	4	S43 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
45	BRS		S43 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
46	BRS	4	S44 S45	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
47	BRS	0	memes.clm. and "display.clm"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
48	BRS	208974	display.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
49	BRS	2084	mems.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
50	BRS	170	S48 and S49	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

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	Type	Hits			Search Text	DBs
بر 1	ממ	۲	250	טעפ	1	US-PGPUB; USPAT;
ł)	})))	5		T; IBM
						US-PGPUB; USPAT;
52	BRS	56	S ₅₀	and	@rlad<"19990701"	USOCR; EPO; JPO;
						DERWENT; IBM_TDB
						US-PGPUB; USPAT;
23	BRS	57	S51	S 52	<u>P.</u>	JSOCR; EPO; JPO;
						DERWENT; IBM_TDB
						US-PGPUB; USPAT;
54	BRS	1057	S49	and	substrate.clm.	_
	-					DERWENT; IBM TDB
						US-PGPUB; USPAT;
52	BRS	275	S54	and	semiconductor.clm.	USOCR; EPO; JPO;
						DERWENT; IBM_TDB
						US-PGPUB; USPAT;
26	BRS	4	S 5 5 5	and	@ad<"19990701"	_
	-					DERWENT; IBM_TDB
			-			US-PGPUB; USPAT;
57	BRS	48	S 55	and	@rlad<"19990701"	Д
						DERWENT; IBM_TDB
						US-PGPUB; USPAT;
28	BRS	50	S56	S57		Щ
						DERWENT; IBM_TDB
						US-PGPUB; USPAT;
59	IS&R	2	("5324		980").PN.	USOCR; EPO; JPO;
						DERWENT; IBM TDB
	-		/ II /	* * * * *	("M) wt propert Ecilicorpoort Ecosidio 6 / 11 /	US-PGPUB; USPAT;
09	IS&R	0	7. Y.	זמד רג	, ,	PO; J
			•			DERWENT; IBM_TDB

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	Type	Hits	Search Text	DBs
2	RRS	388	quartz near15 silicon near15 oxidiz\$4	US-PGPUB; USPAT; USOCR; EPO; JPO;
])				T; IBM
				US-PGPUB; USPAT;
62	BRS	2474	quartz near3 forming	USOCR; EPO; JPO;
				DERWENT; IBM TDB
				US-PGPUB; USPAT;
63	BRS	113	quartz near3 forming near15 oxid\$4	PO; J
				DERWENT; IBM_TDB
				US-PGPUB; USPAT;
64	BRS	1433	quartz nearl (forming or process)	USOCR; EPO; JPO;
				DERWENT; IBM TDB
				US-PGPUB; USPAT;
65	BRS	1433	quartz near (forming or process)	USOCR; EPO; JPO;
				DERWENT; IBM_TDB
				US-PGPUB; USPAT;
99	BRS	29	S64 same (silicon with oxid\$4)	USOCR; EPO; JPO;
				DERWENT; IBM_TDB
				US-PGPUB; USPAT;
29	BRS	21060	quartz.ti.	USOCR; EPO; JPO;
<u>-</u>				DERWENT; IBM_TDB
				US-PGPUB; USPAT;
89	BRS	375126	substrate.ti.	USOCR; EPO; JPO;
,		•		DERWENT; IBM TDB
				US-PGPUB; USPAT;
69	BRS	4364356	(forming or method or fabricating).ti.	USOCR; EPO; JPO;
				DERWENT; IBM_TDB
				US-PGPUB; USPAT;
20	BRS	275	S67 and S68 and S69	PO; J
,		,		DERWENT; IBM TDB

	Type	Hits	Search Text	DBs
71	BRS	1888256	transparent near15 semiconductor nea3 substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
72	BRS	1885736	transparent near5 semiconductor nea3 substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
73	BRS	583	transparent near2 semiconductor near1 substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
74	BRS	303	S73 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
75	BRS	29	S73 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
92	BRS	325	S74 S75	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
7.7	BRS	0	mems and S76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
78	BRS	41	led and S76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
79	BRS	109	display and S76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
80	BRS	91	(transparent near semiconductor) near substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
81	BRS	51	S80 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
82	BRS	1	S80 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
83	BRS	9	S81 S82	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
84	BRS	25	(liquid adj crystal adj display or lcd) and S80	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
85	BRS	9	S84 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
86	BRS	œ	S84 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
87	BRS	13	285 S86	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB